INTEGRATED CIRCUITS

DATA SHEET



74ABT10Triple 3-input NAND gate

Product specification

1995 Sep 22

IC23 Data Handbook





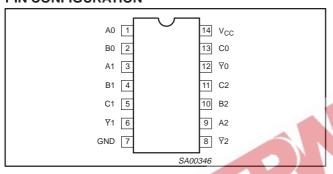
Triple 3-input NAND gate

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QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS $T_{amb} = 25^{\circ}C;$ $GND = 0V$	TYPICAL	UNIT
^t PLH ^t PHL	Propagation delay An, Bn, Cn to Yn	C _L = 50pF; V _{CC} = 5V	3.3 2.2	ns
toslh toshl	Output to Output skew		0.4	ns
C _{IN}	Input capacitance	$V_I = 0V \text{ or } V_{CC}$	3	pF
Icc	Total supply current	Outputs disabled; V _{CC} = 5.5V	50	μΑ

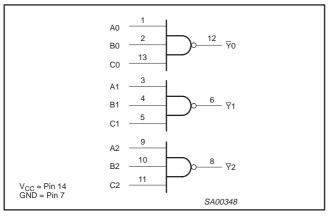
PIN CONFIGURATION



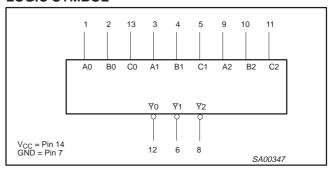
PIN DESCRIPTION

PIN NUMBER	SYMBOL	NAME AND FUNCTION
1, 2, 3, 4, 5, 9, 10, 11, 13	An, Bn, Cn	Data inputs
6, 8, 12	₹n	Data outputs
7	GND	Ground (0V)
14	V _{CC}	Positive supply voltage

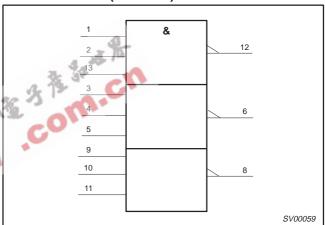
LOGIC DIAGRAM



LOGIC SYMBOL



LOGIC SYMBOL (IEEE/IEC)



FUNCTION TABLE

	INPUTS		OUTPUTS
An	Bn	Cn	₹n
L	L	L	Н
L	L	Н	Н
L	Н	L	Н
L	Н	Н	Н
Н	L	L	Н
Н	L	Н	Н
Н	Н	L	Н
Н	Н	Н	L

NOTES:

H = High voltage level
L = Low voltage level

ORDERING INFORMATION

PACKAGES	TEMPERATURE RANGE	OUTSIDE NORTH AMERICA	NORTH AMERICA	DWG NUMBER
14-Pin Plastic DIP	–40°C to +85°C	74ABT10 N	74ABT10 N	SOT27-1
14-Pin plastic SO	–40°C to +85°C	74ABT10 D	74ABT10 D	SOT108-1
14-Pin Plastic SSOP Type II	-40°C to +85°C	74ABT10 DB	74ABT10 DB	SOT337-1
14-Pin Plastic TSSOP Type I	-40°C to +85°C	74ABT10 PW	74ABT10PW DH	SOT402-1

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ABSOLUTE MAXIMUM RATINGS^{1, 2}

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V _{CC}	DC supply voltage		-0.5 to +7.0	V
I _{IK}	DC input diode current	V _I < 0	-18	mA
VI	DC input voltage ³		-1.2 to +7.0	V
I _{OK}	DC output diode current	V _O < 0	-50	mA
V _{OUT}	DC output voltage ³	output in Off or High state	-0.5 to +5.5	V
I _{OUT}	DC output current	output in Low state	40	mA
T _{stg}	Storage temperature range		-65 to 150	°C

NOTES:

- Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the
 device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to
 absolute-maximum-rated conditions for extended periods may affect device reliability.
- 2. The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability. The maximum junction temperature of this integrated circuit should not exceed 150°C.
- 3. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER		36.30	LIM	ITS	UNIT	
STWIBOL	PARAMETER		40 X 12	MIN	MAX	0,4,1	
V _{CC}	DC supply voltage	4	132	4.5	5.5	V	
V _I	Input voltage		C	0	V _{CC}	V	
V _{IH}	High-level input voltage	•		2.0		V	
V_{IL}	Low-level input voltage				0.8	V	
I _{OH}	High-level output current				– 15	mA	
I _{OL}	Low-level output current				20	mA	
Δt/Δν	Input transition rise or fall rate			0	10	ns/V	
T _{amb}	Operating free-air temperature range			-40	+85	°C	

DC ELECTRICAL CHARACTERISTICS

					LIMITS			
SYMBOL	PARAMETER	TEST CONDITIONS	Tai	_{mb} = +25	°C	T _{amb} =	-40°C 85°C	UNIT
			MIN	TYP	MAX	MIN	MAX	1
V _{IK}	Input clamp voltage	$V_{CC} = 4.5V; I_{IK} = -18mA$		-0.9	-1.2		-1.2	V
V _{OH}	High-level output voltage	$V_{CC} = 4.5V$; $I_{OH} = -15mA$; $V_I = V_{IL}$ or V_{IH}	2.5	2.9		2.5		V
V _{OL}	Low-level output voltage	$V_{CC} = 4.5V$; $I_{OL} = 20mA$; $V_I = V_{IL}$ or V_{IH}		0.35	0.5		0.5	V
lı	Input leakage current	$V_{CC} = 5.5V; V_I = GND \text{ or } 5.5V$		±0.01	±1.0		±1.0	μΑ
I _{OFF}	Power-off leakage current	$V_{CC} = 0.0V$; V_O or $V_I \le 4.5V$		±5.0	±100		±100	μΑ
I _{CEX}	Output High leakage current	$V_{CC} = 5.5V$; $V_O = 5.5V$; $V_I = GND$ or V_{CC}		5.0	50		50	μΑ
ΙO	Output current ¹	$V_{CC} = 5.5V; V_O = 2.5V$	-50	-75	-180	-50	-180	mA
Icc	Quiescent supply current	$V_{CC} = 5.5V$; $V_I = GND$ or V_{CC}		2	50		50	μΑ
Δl _{CC}	Additional supply current per input pin ²	V_{CC} = 5.5V; One data input at 3.4V, other inputs at V_{CC} or GND		0.25	500		500	μА

NOTES:

- 1. Not more than one output should be tested at a time, and the duration of the test should not exceed one second.
- 2. This is the increase in supply current for each input at 3.4V.
- 3. For valid test results, data must not be loaded into the flip-flop or latch after applying the power.

Triple 3-input NAND gate

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AC CHARACTERISTICS

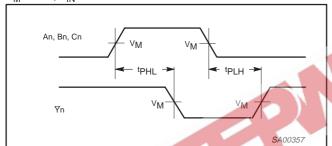
GND = 0V; t_R = t_F = 2.5ns; C_L = 50pF, R_L = 500 Ω

SYMBOL PARAMETER	PARAMETER	WAVEFORM	T _a	_{amb} = +25° 'CC = +5.0	C V	T _{amb} = -40° V _{CC} = +5.	UNIT	
			MIN	TYP	MAX	MIN	MAX	
t _{PLH} t _{PHL}	Propagation delay An, Bn, Cn to Yn	1	1.0 1.0	3.3 2.2	4.7 3.3	1.0 1.0	5.3 3.7	ns
toshl toshh ¹	Output to Output skew An or Bn to ∀n	2		0.4	0.5		0.5	ns

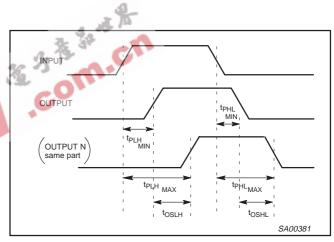
NOTE:

AC WAVEFORMS

 $V_{M} = 1.5V, V_{IN} = GND \text{ to } 3.0V$

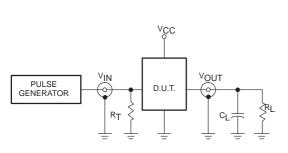


Waveform 1. Propagation Delay for Inverting Outputs



Waveform 2. Common edge skew

TEST CIRCUIT AND WAVEFORMS



Test Circuit for Outputs

AMP (V) 90% NEGATIVE ٧M **PULSE** 10% 10% tTHL (tF) tTLH (tR) tTLH (tR) tTHL (tF) AMP (V) 90% 90% POSITIVE **PULSE** 10% tw $V_{M} = 1.5V$

Input Pulse Definition

FAMILY	Amplitude Rep. Rate t _W t _R				
PAWILT	Amplitude	Rep. Rate	t _W	t _R	t _F
74ABT	3.0V	1MHz	500ns	2.5ns	2.5ns

SH00067

DEFINITIONS

R_L = Load resistor; see AC CHARACTERISTICS for value.

C_L = Load capacitance includes jig and probe capacitance; see AC CHARACTERISTICS for value.

R_T = Termination resistance should be equal to Z_{OUT} of pulse generators.

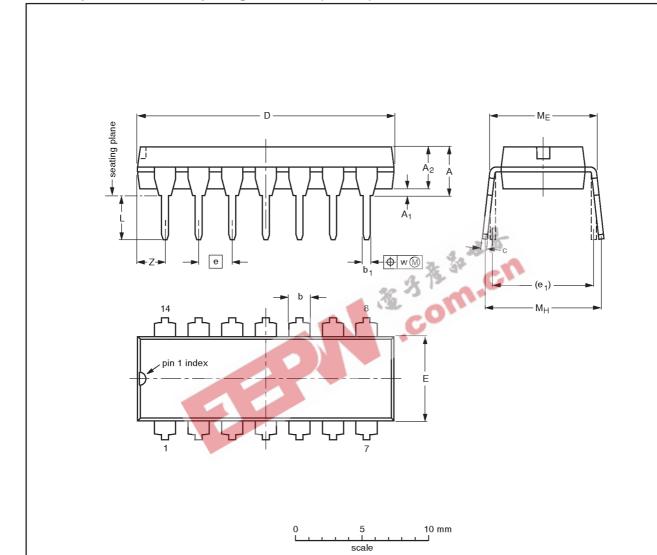
Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

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DIP14: plastic dual in-line package; 14 leads (300 mil)

SOT27-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁ min.	A ₂ max.	b	b ₁	С	D ⁽¹⁾	E ⁽¹⁾	е	e ₁	L	ME	M _H	w	Z ⁽¹⁾ max.
mm	4.2	0.51	3.2	1.73 1.13	0.53 0.38	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	2.2
inches	0.17	0.020	0.13	0.068 0.044	0.021 0.015	0.014 0.009	0.77 0.73	0.26 0.24	0.10	0.30	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.087

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

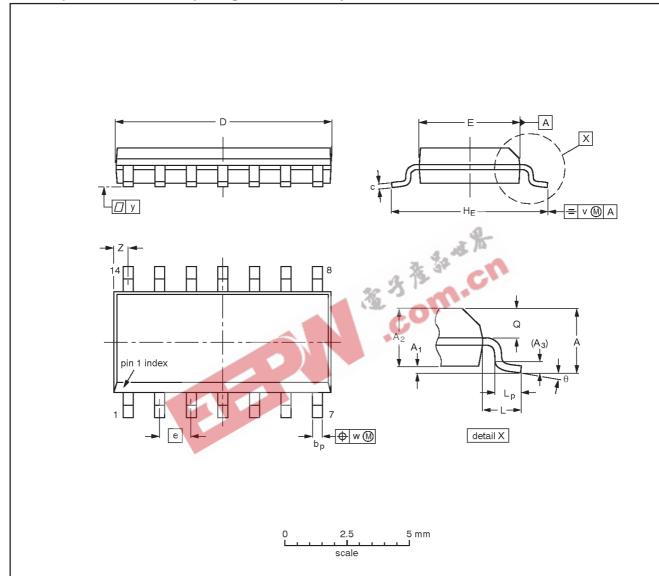
OUTLINE		REFER	RENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	EIAJ	PROJECTION	ISSUE DATE
SOT27-1	050G04	MO-001AA			92-11-17 95-03-11

Triple 3-input NAND gate

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SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

	·																	
UNIT	A max.	A ₁	A ₂	Α3	bp	С	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	8.75 8.55	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.010 0.004	0.057 0.049	0.01		0.0100 0.0075		0.16 0.15	0.050	0.244 0.228	0.041	0.039 0.016		0.01	0.01	0.004	0.028 0.012	o°

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

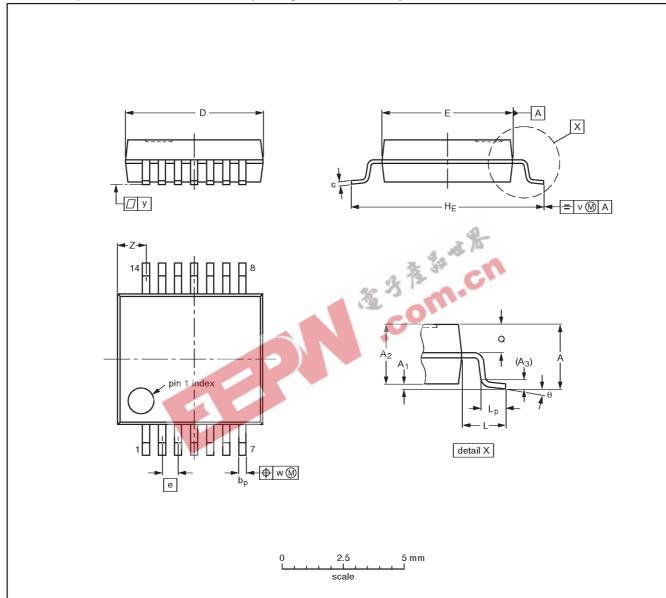
OUTLINE		REFEF	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
SOT108-1	076E06S	MS-012AB				-95-01-23 97-05-22	

Triple 3-input NAND gate

74ABT10

SSOP14: plastic shrink small outline package; 14 leads; body width 5.3 mm

SOT337-1



DIMENSIONS (mm are the original dimensions)

						,												
UNIT	A max.	Α ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	2.0	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	6.4 6.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.4 0.9	8° 0°

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

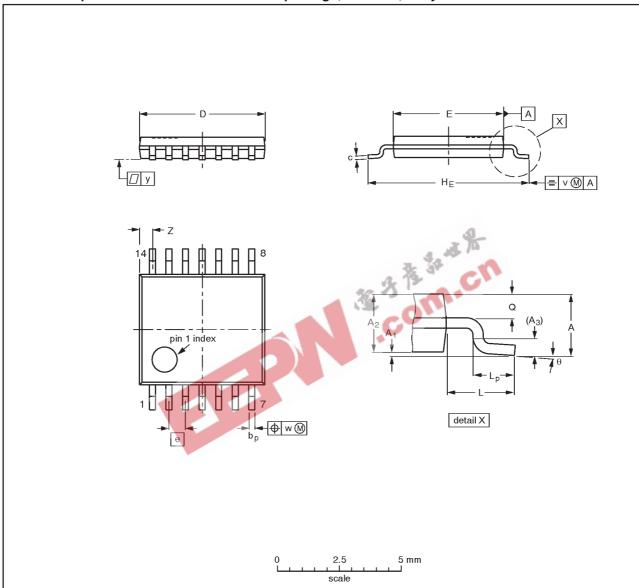
OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
SOT337-1		MO-150AB				-95-02-04 96-01-18	

Triple 3-input NAND gate

74ABT10

TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	Α1	A ₂	А3	рb	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1.10	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1.0	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.72 0.38	8° 0°

Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ICCUE DATE			
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
SOT402-1		MO-153				-94-07-12 95-04-04	

Triple 3-input NAND gate

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DEFINITIONS							
Data Sheet Identification	Product Status	Definition					
Objective Specification	Formative or in Design	This data sheet contains the design target or goal specifications for product development. Specifications may change in any manner without notice.					
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(print code) Date of release: July 1994

Document order number: 9397-750-04851